

Features

- Single Biasing Voltage (Self Biased)
- Frequency: 1-9GHz
- Small Signal Gain: 28dB
- Noise Figure: 0.7 dB typ.
- P1dB: 14dBm
- Power supply: +5V/67mA
- Input/Output: 50Ω
- Die Size: 1.85 x 1.25 x 0.09 mm

Typical Applications

- Test Instrumentation
- Microwave Radio & VSAT
- Military & Space
- Telecom Infrastructure
- Fiber Optics

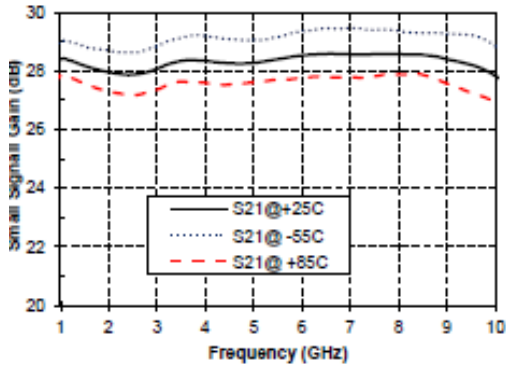
Electrical Specifications

TA = +25°C, Vd = +5V

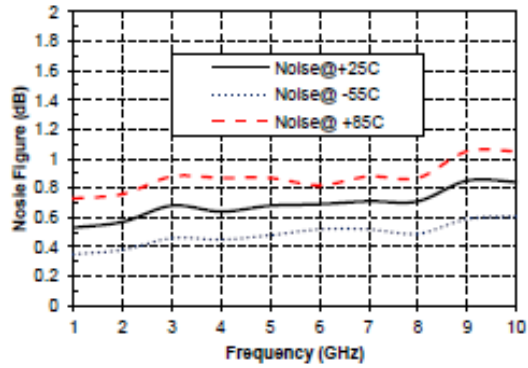
Parameters	Min.	Typ.	Max.	Units
Frequency	1-9			GHz
Small Signal Gain	27	28	29.5	dB
Gain Flatness		±0.5		dB
Noise Figure		0.7		dB
Output 1dB Compression (P1dB)		14		dBm
Saturated Output Power (Psat)		15		dBm
Input Return Loss		11		dB
Output Return Loss		14		dB
Static current	50	67	80	mA



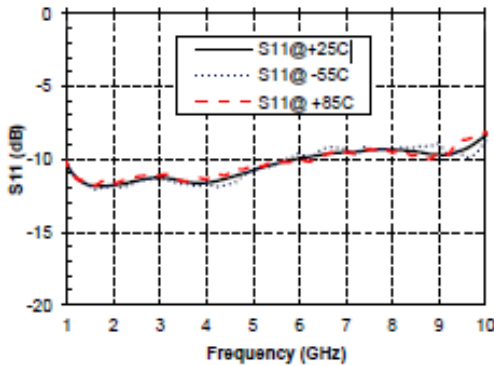
Gain vs. Frequency



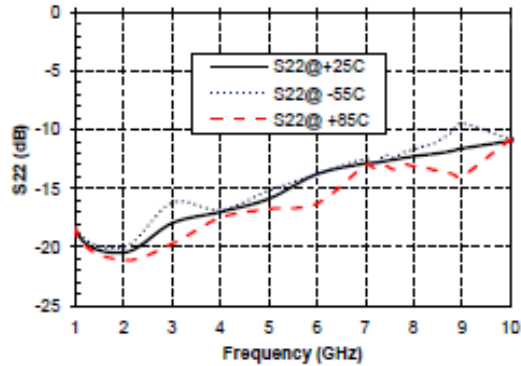
Noise Figure vs. Frequency



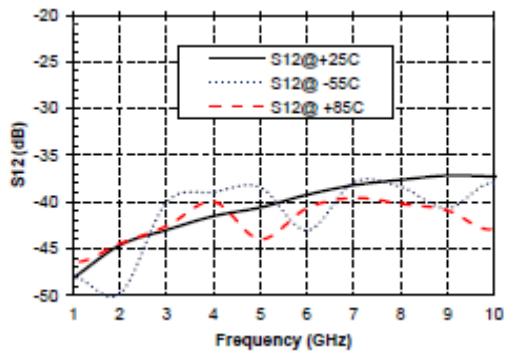
Input Return Loss vs. Frequency



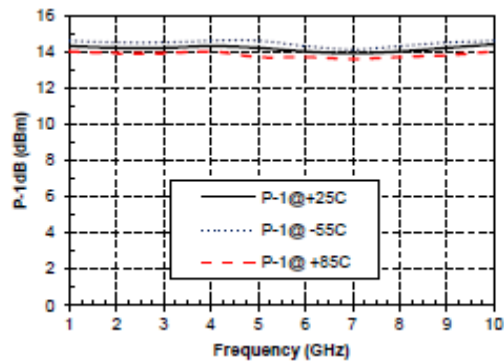
Output Return Loss vs. Frequency



Reverse Isolation vs. Frequency

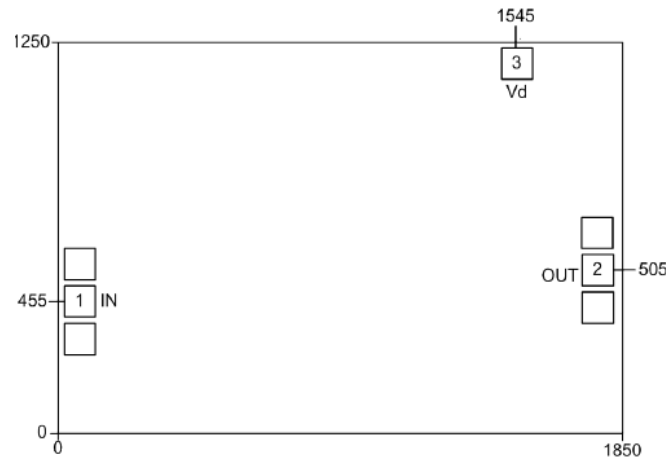


P1dB vs. Frequency





Outline Drawing:
All Dimensions in μm

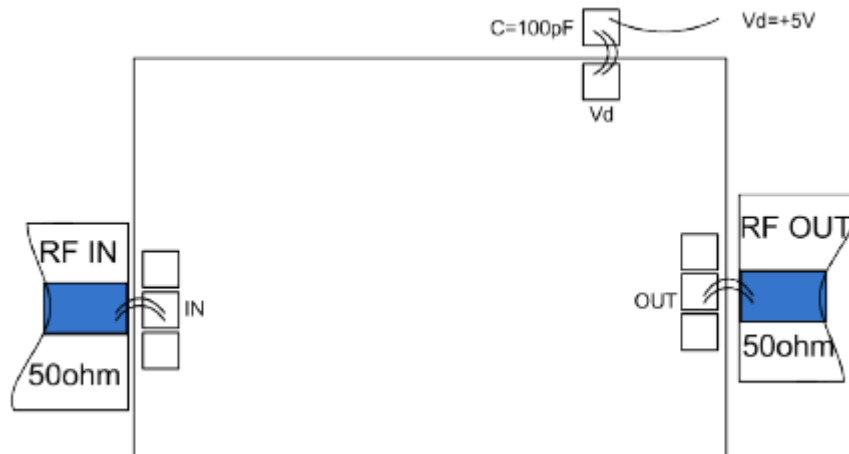


Pad Description

Pad	Function	Description
1	RF IN	RF signal input terminal, blocking capacitor required.
2	RF OUT	RF signal output terminal, no blocking capacitor required.
3	VDD	Amplifier drain bias; external 100pF bypass capacitor required.
Die bottom	GND	Die bottom must be connected to RF/DC ground.



Assembly Drawing



Notes:

1. Die thickness: 100um
2. Typical bond pad is 100*100 μm^2
3. Bond pad metalization: Gold
4. Backside metalization: Gold
5. Backside of the die (GND)
6. No connection required for unlabeled bond pads

Maximum Ratings:

1. Maximum drain voltage: +7V
2. Maximum input power: +20dBm
3. Operating temperature: -55°C to +85°C
4. Storage temperature: -65°C to +150°C